

**Polar3™ HiPerFET™  
Power MOSFETs**
**IXFK150N30P3  
IXFX150N30P3**

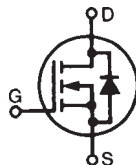
$$V_{DSS} = 300V$$

$$I_{D25} = 150A$$

$$R_{DS(on)} \leq 19m\Omega$$

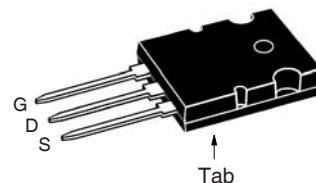
$$t_{rr} \leq 250ns$$

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

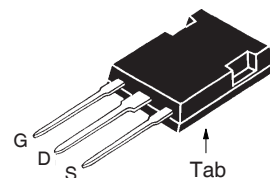


| Symbol        | Test Conditions  | Maximum Ratings   |            |
|---------------|--|-------------------|------------|
| $V_{DSS}$     | $T_J = 25^\circ C$ to $150^\circ C$                                | 300               | V          |
| $V_{DGR}$     | $T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$          | 300               | V          |
| $V_{GSS}$     | Continuous   | $\pm 20$          | V          |
| $V_{GSM}$     | Transient  | $\pm 30$          | V          |
| $I_{D25}$     | $T_C = 25^\circ C$   | 150               | A          |
| $I_{DM}$      | $T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$               | 375               | A          |
| $I_A$         | $T_C = 25^\circ C$   | 75                | A          |
| $E_{AS}$      | $T_C = 25^\circ C$   | 4                 | J          |
| $P_D$         | $T_C = 25^\circ C$   | 1300              | W          |
| $dv/dt$       | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$ | 35                | V/ns       |
| $T_J$         |  | -55 ... +150      | $^\circ C$ |
| $T_{JM}$      |  | 150               | $^\circ C$ |
| $T_{stg}$     |  | -55 ... +150      | $^\circ C$ |
| $T_L$         | 1.6mm (0.062 in.) from Case for 10s                                | 300               | $^\circ C$ |
| $T_{SOLD}$    | Plastic Body for 10s   | 260               | $^\circ C$ |
| $M_d$         | Mounting Torque (TO-264)   | 1.13/10           | Nm/lb.in.  |
| $F_c$         | Mounting Force (PLUS247)   | 20..120 / 4.5..27 | N/lb.      |
| <b>Weight</b> | TO-264   | 10                | g          |
|               | PLUS247  | 6                 | g          |

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate      D = Drain  
S = Source      Tab = Drain

**Features**

- Dynamic dv/dt Rating
- Avalanche Rated
- Fast Intrinsic Diode
- Low  $Q_G$
- Low  $R_{DS(on)}$
- Low Drain-to-Tab Capacitance
- Low Package Inductance

**Advantages**

- Easy to Mount
- Space Savings

**Applications**

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- High Speed Power Switching Applications

| Symbol       | Test Conditions<br>( $T_J = 25^\circ C$ Unless Otherwise Specified) | Characteristic Values |      |                    |
|--------------|---|-----------------------|------|--------------------|
|              |   | Min.                  | Typ. | Max.               |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 3mA$   | 300                   |      | V                  |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 8mA$                                     | 3.0                   |      | 5.0 V              |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                                  |                       |      | $\pm 200$ nA       |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 125^\circ C$           |                       |      | 25 $\mu A$<br>1 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                 |                       |      | 19 m $\Omega$      |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)  | Characteristic Values |       |                    |
|--------------|--|-----------------------|-------|--------------------|
|              |  | Min.                  | Typ.  | Max.               |
| $g_{fs}$     | $V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1   | 65                    | 110   | S                  |
| $C_{iss}$    | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$   |                       | 12.1  | nF                 |
| $C_{oss}$    |  |                       | 1910  | pF                 |
| $C_{rss}$    |  |                       | 40    | pF                 |
| $R_{Gi}$     | Gate Input Resistance  |                       | 1.0   | $\Omega$           |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$<br>$R_G = 1\Omega$ (External) |                       | 44    | ns                 |
| $t_r$        |  |                       | 30    | ns                 |
| $t_{d(off)}$ |  |                       | 74    | ns                 |
| $t_f$        |  |                       | 12    | ns                 |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$   |                       | 197   | nC                 |
| $Q_{gs}$     |  |                       | 70    | nC                 |
| $Q_{gd}$     |  |                       | 65    | nC                 |
| $R_{thJC}$   |  |                       | 0.096 | $^\circ\text{C/W}$ |
| $R_{thCS}$   |  | 0.15                  |       | $^\circ\text{C/W}$ |

### Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified) | Characteristic Values |      |        |
|----------|---|-----------------------|------|--------|
|          |   | Min.                  | Typ. | Max.   |
| $I_S$    | $V_{GS} = 0\text{V}$  |                       |      | 150 A  |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$                                 |                       |      | 600 A  |
| $V_{SD}$ | $I_F = 100\text{A}, V_{GS} = 0\text{V}$ , Note 1                            |                       |      | 1.5 V  |
| $t_{rr}$ | $I_F = 75\text{A}, -di/dt = 100\text{A}/\mu\text{s}$                        |                       |      | 250 ns |
| $Q_{RM}$ |   |                       | 2.9  |        |
| $I_{RM}$ | $V_R = 100\text{V}, V_{GS} = 0\text{V}$                                     |                       | 23.0 | A      |

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

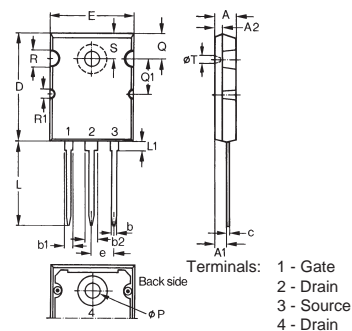
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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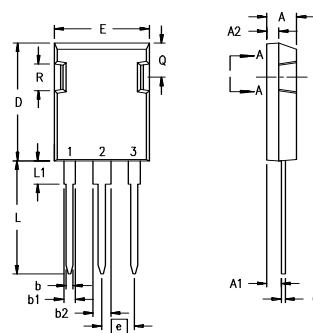
IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

### TO-264 AA Outline



| Dim. | Millimeter |       | Inches   |       |
|------|------------|-------|----------|-------|
|      | Min.       | Max.  | Min.     | Max.  |
| A    | 4.82       | 5.13  | .190     | .202  |
| A1   | 2.54       | 2.89  | .100     | .114  |
| A2   | 2.00       | 2.10  | .079     | .083  |
| b    | 1.12       | 1.42  | .044     | .056  |
| b1   | 2.39       | 2.69  | .094     | .106  |
| b2   | 2.90       | 3.09  | .114     | .122  |
| c    | 0.53       | 0.83  | .021     | .033  |
| D    | 25.91      | 26.16 | 1.020    | 1.030 |
| E    | 19.81      | 19.96 | .780     | .786  |
| e    | 5.46 BSC   |       | .215 BSC |       |
| J    | 0.00       | 0.25  | .000     | .010  |
| K    | 0.00       | 0.25  | .000     | .010  |
| L    | 20.32      | 20.83 | .800     | .820  |
| L1   | 2.29       | 2.59  | .090     | .102  |
| P    | 3.17       | 3.66  | .125     | .144  |
| Q    | 6.07       | 6.27  | .239     | .247  |
| Q1   | 8.38       | 8.69  | .330     | .342  |
| R    | 3.81       | 4.32  | .150     | .170  |
| R1   | 1.78       | 2.29  | .070     | .090  |
| S    | 6.04       | 6.30  | .238     | .248  |
| T    | 1.57       | 1.83  | .062     | .072  |

### PLUS 247™ Outline



Terminals: 1 - Gate  
2 - Drain  
3 - Source

| Dim. | Millimeter |       | Inches   |       |
|------|------------|-------|----------|-------|
|      | Min.       | Max.  | Min.     | Max.  |
| A    | 4.83       | 5.21  | .190     | .205  |
| A1   | 2.29       | 2.54  | .090     | .100  |
| A2   | 1.91       | 2.16  | .075     | .085  |
| b    | 1.14       | 1.40  | .045     | .055  |
| b1   | 1.91       | 2.13  | .075     | .084  |
| b2   | 2.92       | 3.12  | .115     | .123  |
| C    | 0.61       | 0.80  | .024     | .031  |
| D    | 20.80      | 21.34 | .819     | .840  |
| E    | 15.75      | 16.13 | .620     | .635  |
| e    | 5.45 BSC   |       | .215 BSC |       |
| L    | 19.81      | 20.32 | .780     | .800  |
| L1   | 3.81       | 4.32  | .150     | .170  |
| Q    | 5.59       | 6.20  | .220     | 0.244 |
| R    | 4.32       | 4.83  | .170     | .190  |

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

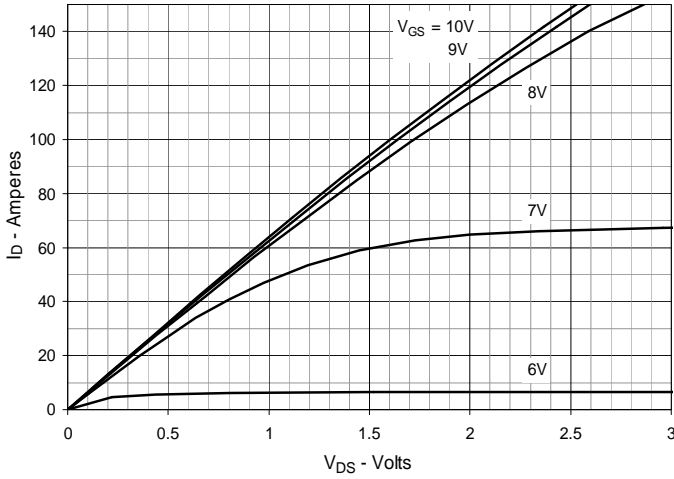


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

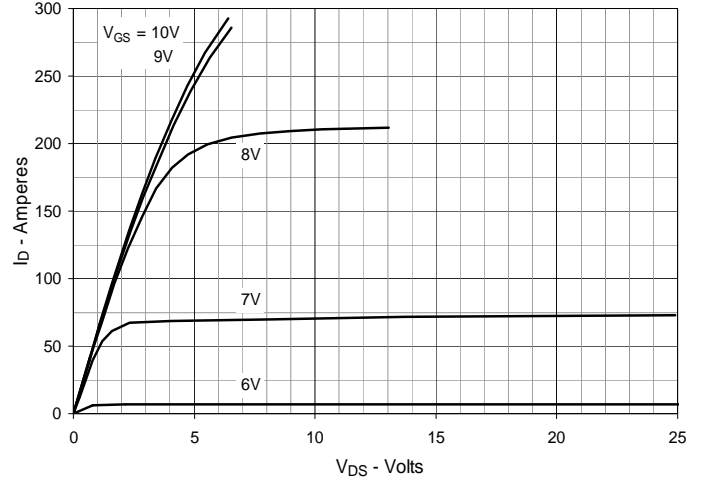


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

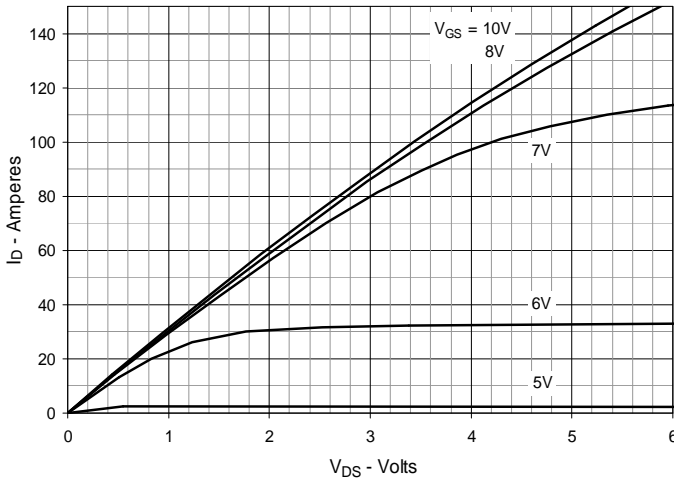


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 75\text{A}$  Value vs. Junction Temperature

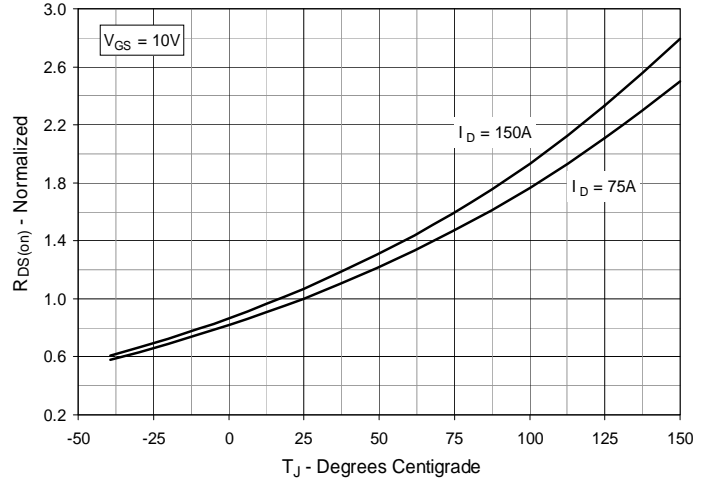


Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 75\text{A}$  Value vs. Drain Current

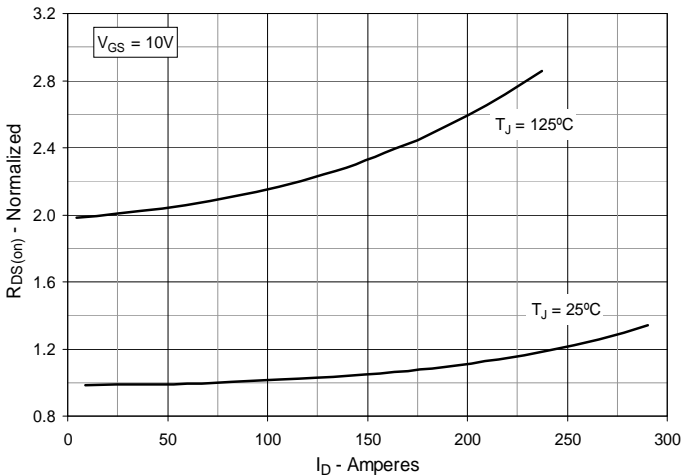
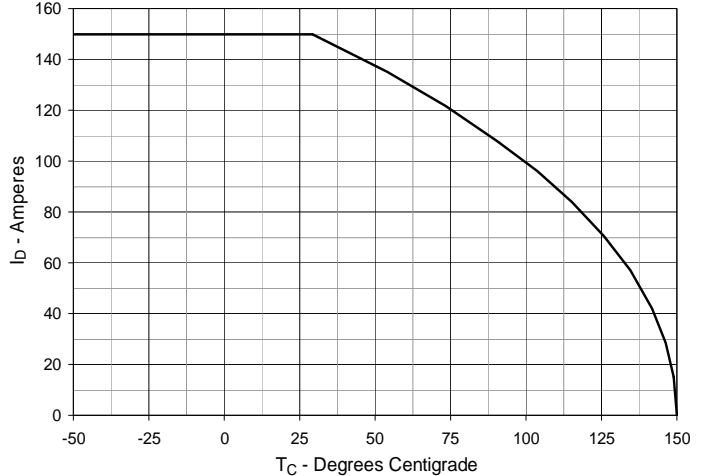
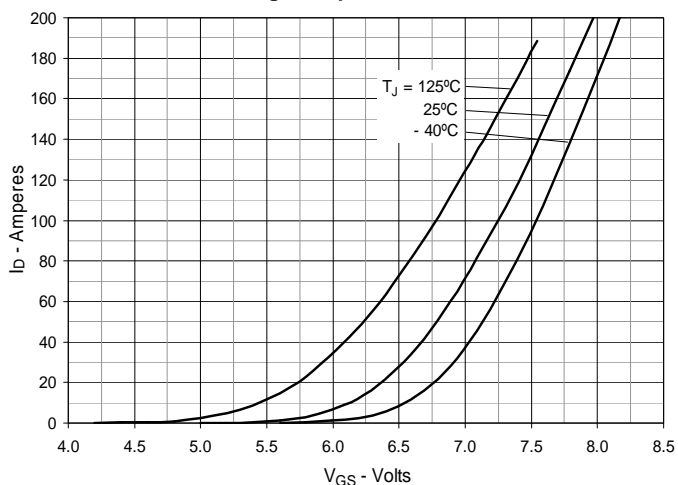


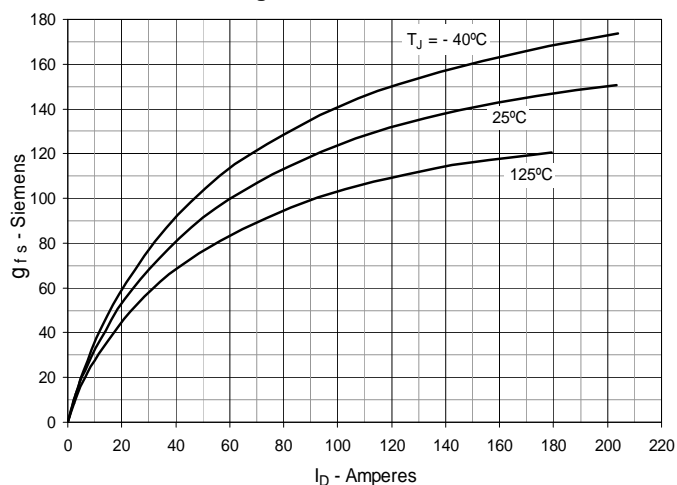
Fig. 6. Maximum Drain Current vs. Case Temperature



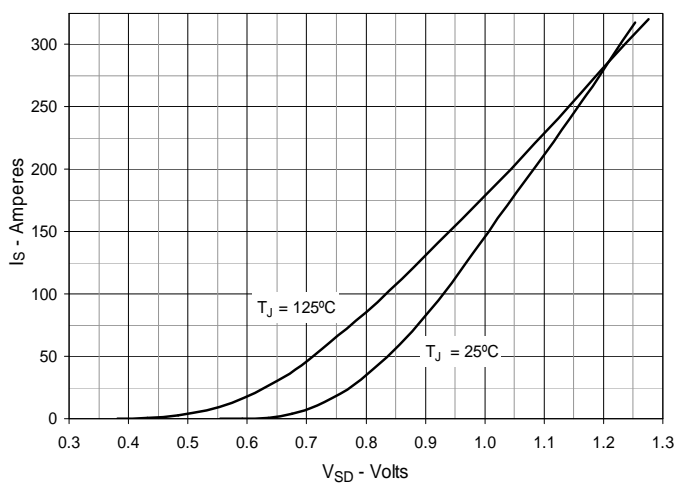
**Fig. 7. Input Admittance**



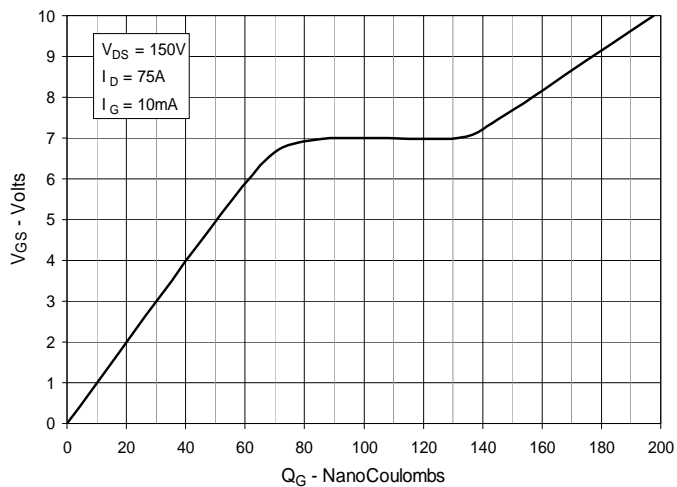
**Fig. 8. Transconductance**



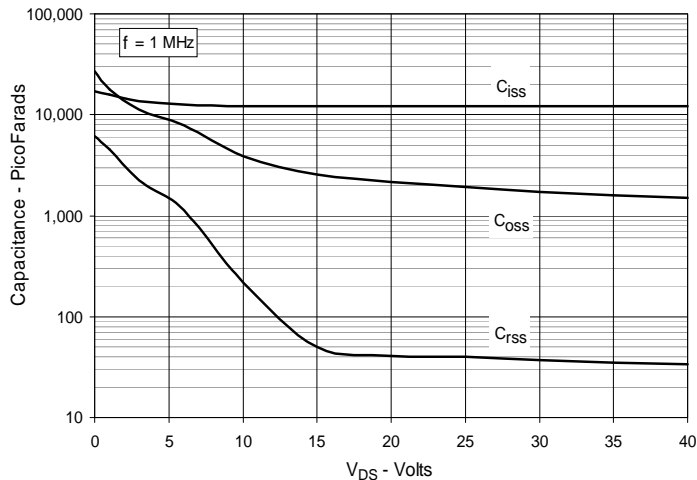
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



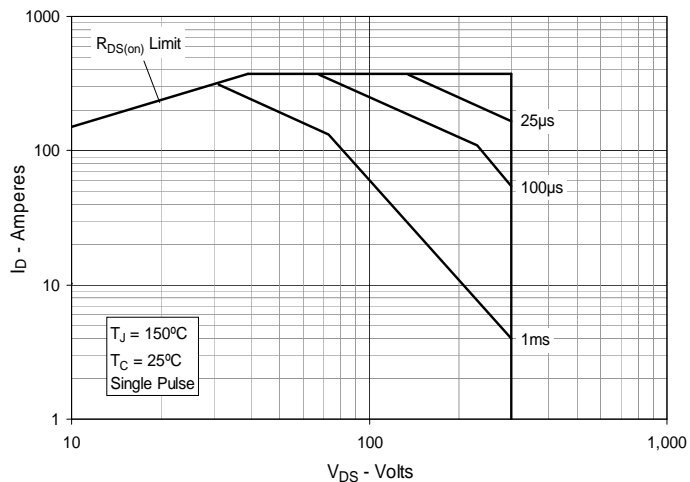
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**



**Fig. 13. Maximum Transient Thermal Impedance**

